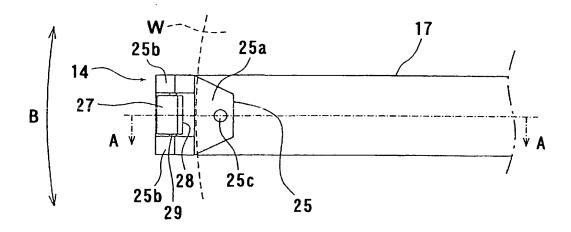
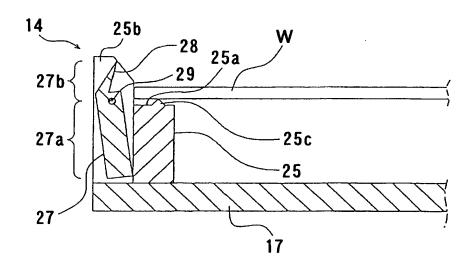


F I G. 2A

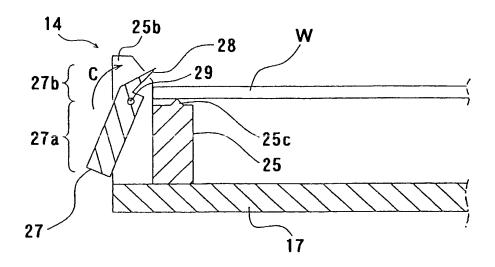


F / G. 2B

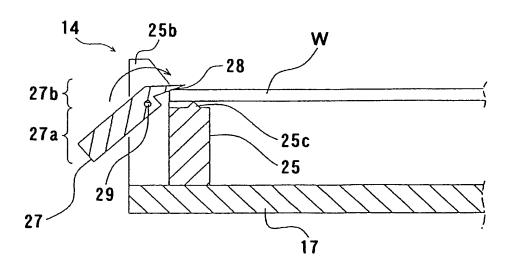


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3/16 F I G. 3 A

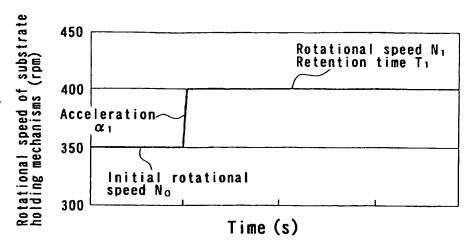


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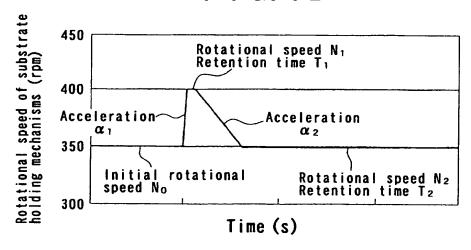


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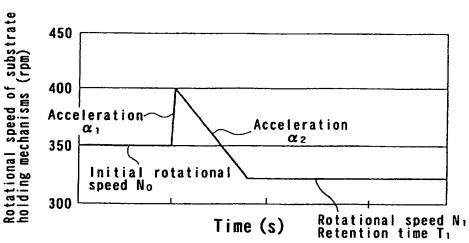
4/16 F I G. 4 A



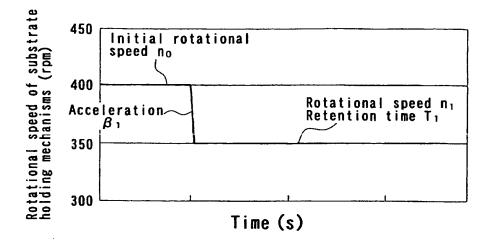
F / G. 4 B



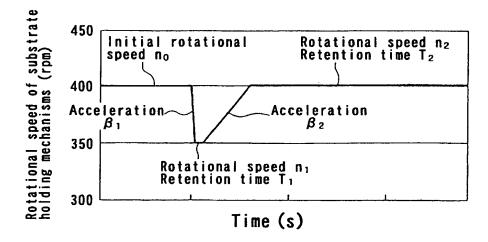
F / G. 4 C



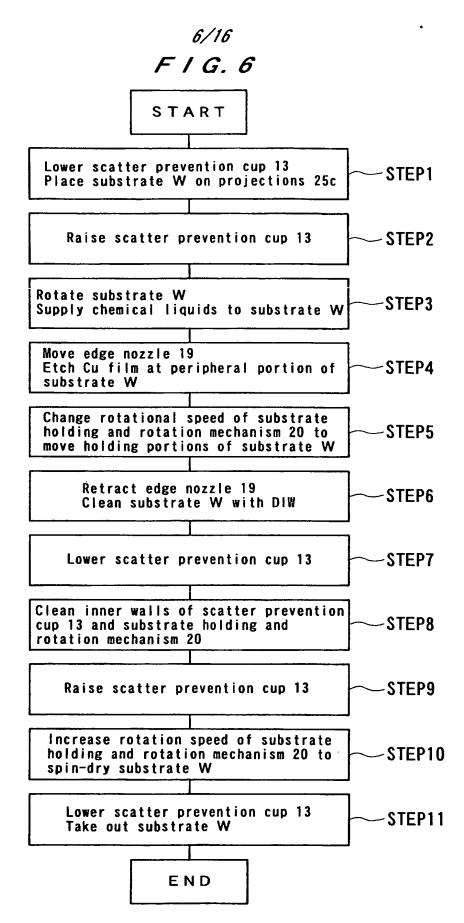
F / G. 5 A

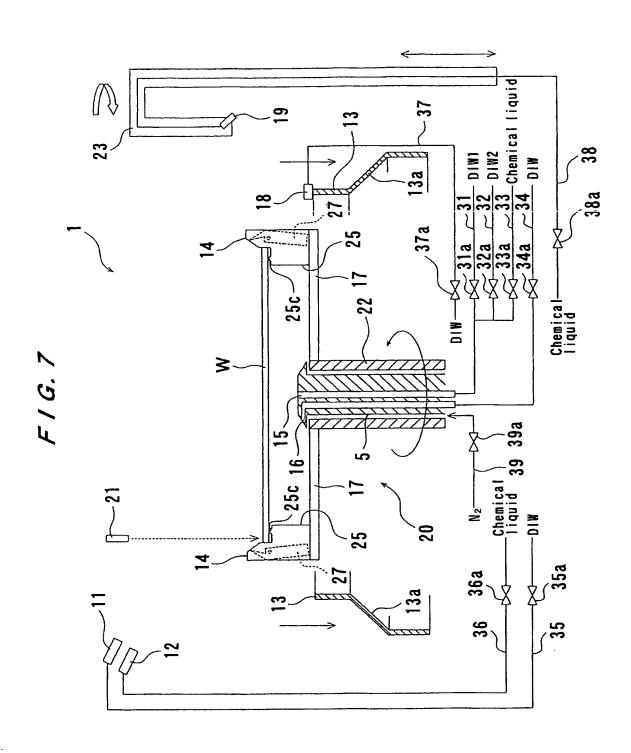


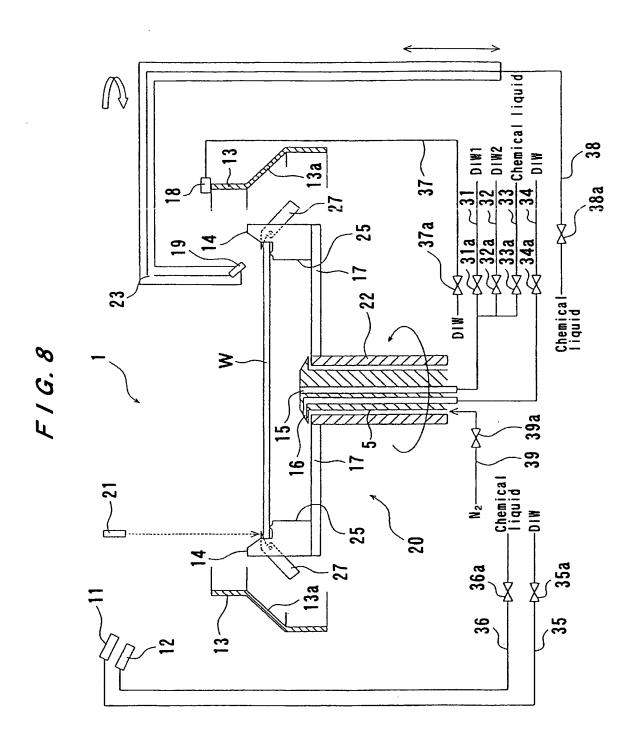
F / G. 5 B

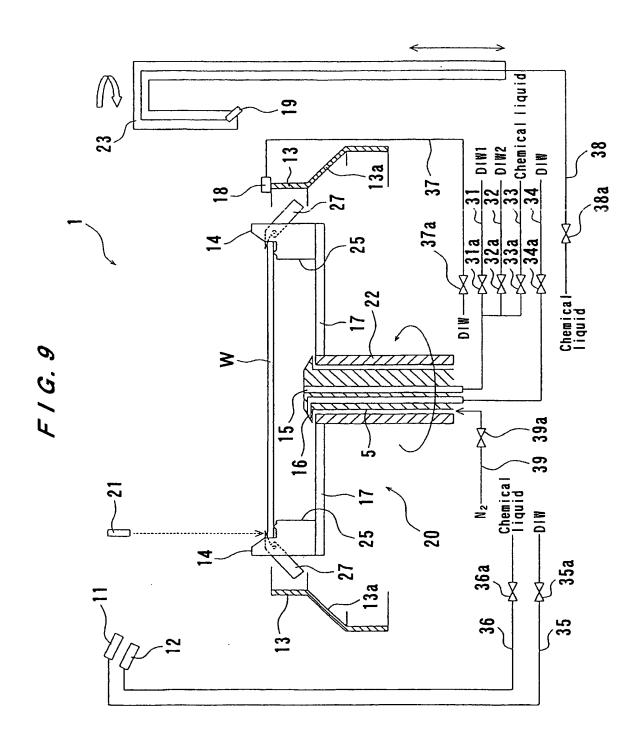


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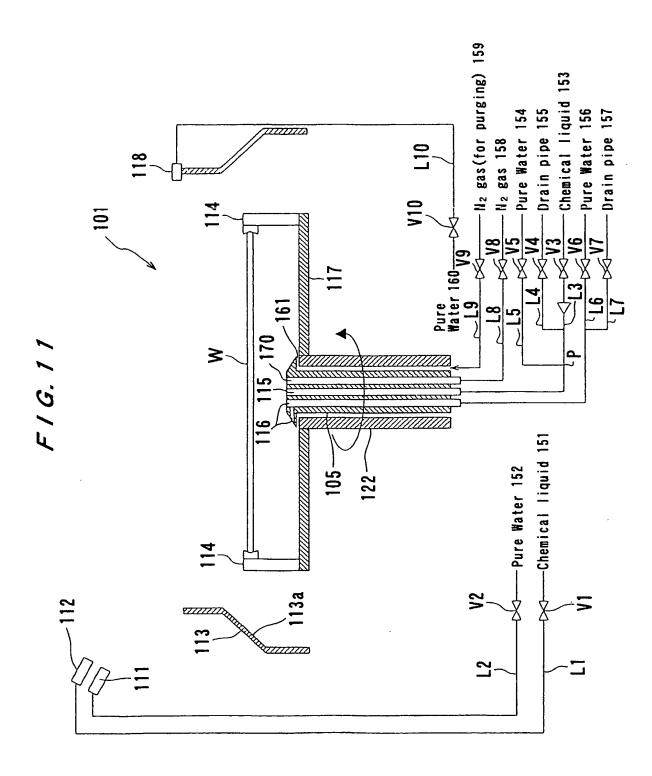


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F I G. 10

START Lower scatter prevention cup 13 -STEP1 Place substrate W on projections 25c Raise scatter prevention cup 13 -STEP2 Rotate substrate W -STEP3 Supply chemical liquids to substrate W Move edge nozzle 19 -STEP4 Etch Cu film at peripheral portion of substrate W Change rotational speed of substrate holding and rotation mechanism 20 to move holding portions of -STEP5 substrate W Start supply of DIW to substrate W -STEP6 Stop supply of chemical liquid Supply DIW to front and back surfaces of substrate W to clean substrate W -STEP7 Clean nozzles 15 and 16 Increase rotational speed of substrate holding and rotation mechanism 20 to remove chemical liquid -STEP8-1 attached to substrate holding mechanisms 14 Decrease rotational speed of substrate holding and rotation mechanism 20 to clean chemical liquid -STEP8-2 attached to substrate holding mechanisms 14 Clean inner walls of scatter -STEP9 prevention cup 13 Raise scatter prevention cup 13 -STEP10 Increase rotational speed of substrate holding and -STEP11 rotational mechanism 20 to spin-dry substrate W Lower scatter prevention cup 13 -STEP12 Take out substrate W

END



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F / G. 12

